

NPN Silicon Epitaxial Planar Transistor

2SC4215

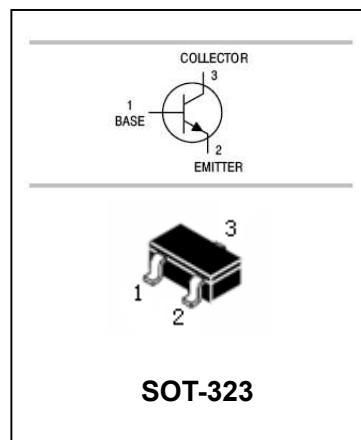
FEATURES

- Small reverse transfer capacitance.
- Low noise figure.



APPLICATIONS

- FM,RF,MIX,IF Amplifier Applications.



ORDERING INFORMATION

Type No.	Marking	Package Code
2SC4215	QR/QO/QY	SOT-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	40	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	4	V
I _C	Collector Current -Continuous	20	mA
I _B	Base Current	4	mA
P _C	Collector Dissipation	150	mW
T _j , T _{stg}	Junction and Storage Temperature	-55 to +150	°C

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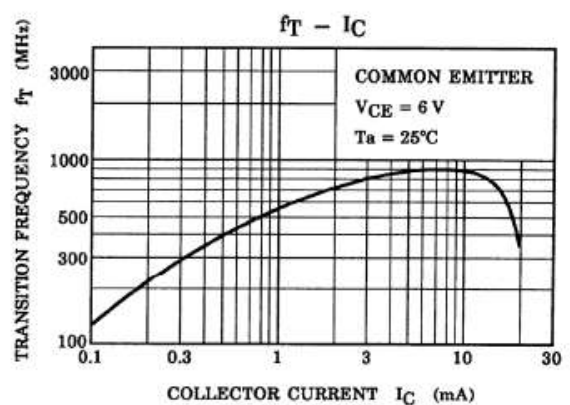
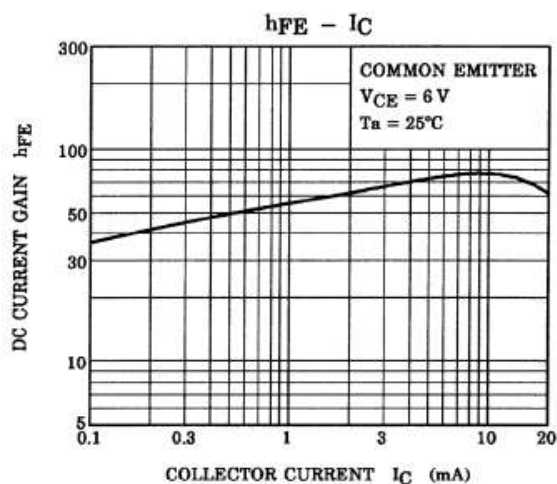
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=40V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			0.5	μA
DC current gain	h_{FE}	$V_{CE}=6V, I_C=1mA$	40		200	
Collector-base time constant	$C_C \cdot r_{bb'}$	$V_{CE}=6V, I_C=1mA$			25	ps
Transition frequency	f_T	$V_{CE}=6V, I_E=1mA$	260	550		MHz

CLASSIFICATION OF h_{FE}

Marking	QR	QO	QY
h_{FE}	40-80	70-140	100-200

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



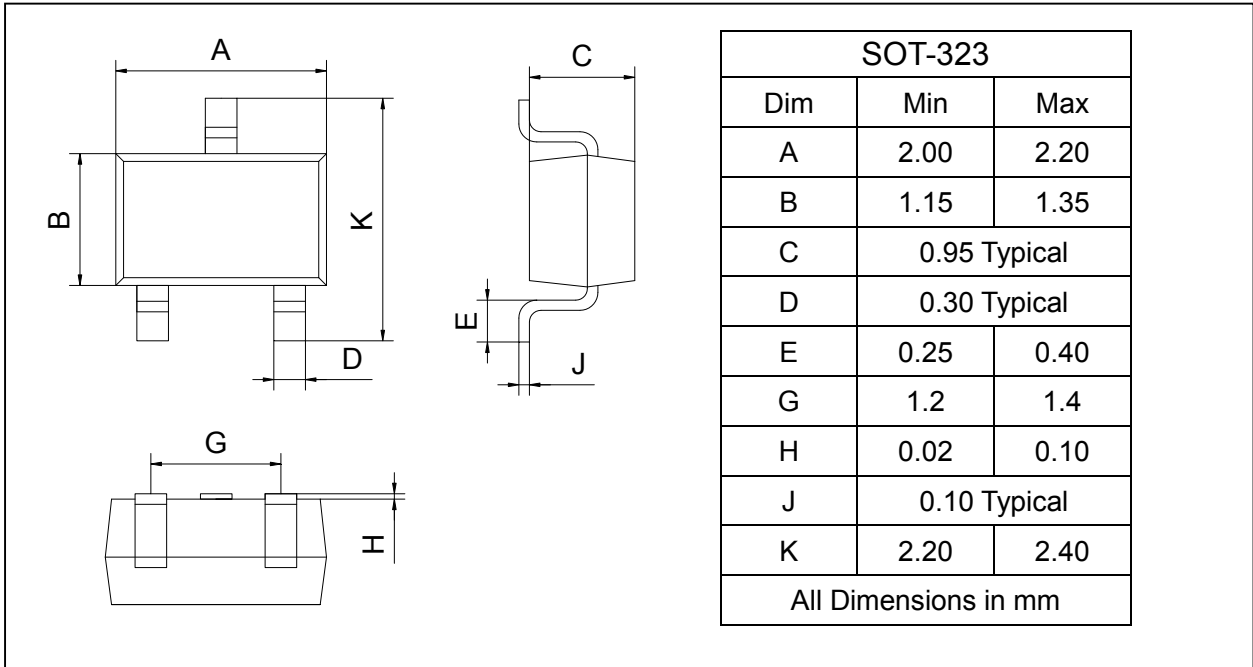
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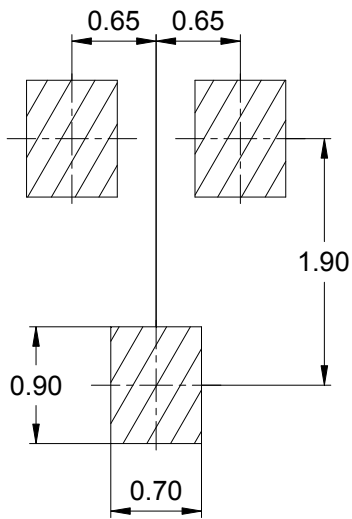
PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SC4215	SOT-323	3000/Tape&Reel